

2SD1632

Silicon NPN Triple-Diffused Junction Mesa Type

Horizontal Deflection Output

■ Features

- Damper diode built-in
- High breakdown voltage and high reliability by glass passivation
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (Tc=25°C)

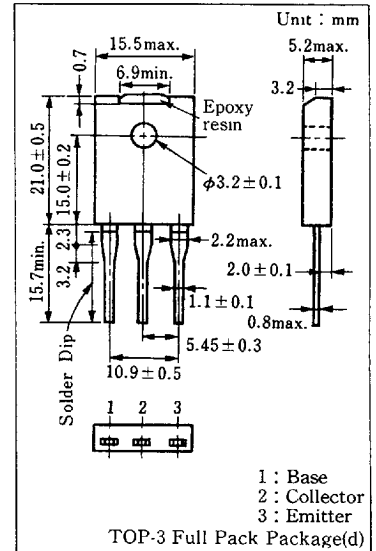
Item	Symbol	Value	Unit	
Collector-base voltage	V_{CBO}	1500	V	
Collector-emitter voltage	V_{CES}	1500	V	
Emitter-base voltage	V_{EBO}	5	V	
Collector current	I_C	4	A	
Peak collector current	I_{CP}^*	15	A	
Peak base current	I_{BP}	3.5	A	
Reverse peak base current	I_{BP}	-2.5	A	
Collector power dissipation	P_C	Tc=25°C	70	W
		Ta=25°C	3	
Junction temperature	T_J	130	°C	
Storage temperature	T_{stg}	-55 ~ +130	°C	

* Non-repetitive peak value

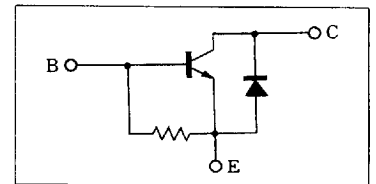
■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB}=750\text{ V}, I_E=0$			50	μA
		$V_{CB}=1500\text{ V}, I_E=0$			1	mA
Emitter-base voltage	V_{EBO}	$I_E=500\text{ mA}, I_C=0$	5			
DC current gain	h_{FE}	$V_{CE}=10\text{ V}, I_C=3\text{ A}$	5		15	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3\text{ A}, I_B=1\text{ A}$			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=3\text{ A}, I_B=1\text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE}=10\text{ V}, I_C=1\text{ A}, f=0.5\text{ MHz}$		2		MHz
Fall time	t_f	$I_C=3\text{ A}, I_{Bend}=1\text{ A}$			0.75	μs
Storage time	t_{stg}	$L_{leak}=5\mu\text{H}$	4		9	μs
Diode forward voltage	V_F	$I_C=-4\text{ A}, I_B=0$			-2.2	V

■ Package Dimensions



■ Inner Circuit



■ 6932852 0016776 486 ■

